PROCESS BATCH SHEET (Oxide Etch) **Issue 7** **Page____of____**

ENSC Batch No.________________________Wafers Started_________________Date_____________________
Material_________________Orientation______________Size_______________Thickness__________________
Resistivity___________________________________Type____
Wafer Vendor__________________________Vendor Batch #___________________SFU P.O._______________

Process Step #	Process Conditions	Oper & Wafer #	Comments
_____A	**Oxide Etch to endpoint** Transene buffered oxide etchant. Slight agitation. Room temp. Etch rate = about 0.1 micron/min. Calculate time to etch but determine endpoint by eye. Note that presence of borosilicate and phosphosilicate glasses will affect oxide etch rate.		Coat the back side of wafer with resist if oxide must remain. This is common for micromachining, but not for semiconductor processing. If the back side is 3 dimensional, the integrity of the resist on the back is questionable. The wafer should then be floated on the surface of the etchant to etch the front side.
_____B	**DI Water Rinse** > 10 minutes in running DI water. Look for dewetting.		
_____C	**Dry** Blow dry with dry N2. Do not spin. Resist contaminates chuck. Spin only furnace ready wafers.		
_____D	**Inspect** Microscope with yellow light. Ensure etch complete. Etch more if needed. Measure if req'd.		Measurement optional if required.
_____E	**Photoresist Strip** Soak in room temp acetone until resist is dissolved. Soak in fresh acetone for a further 1-2 min.		
_____F	**DI Water Rinse** > 3 minutes in running DI water.		
_____G	**Dry** Spin dry or blow dry with N2.		
_____H	**Inspect and Measure** Use microscope. Inspect for remnant resist. If necessary, repeat acetone strip. Measure features if required.		Measurement optional if required. Remnant resist may appear as films or hair like structures.